Bipolar Transistor -160 V, -1 A, Low V_{CE}(sat), PNP Single

This device is bipolar junction transistor featuring high current, low saturation voltage, and high speed switching.

Suitable for automotive applications. AEC-Q101 qualified and PPAP capable.

Features

- Large Current Capacitance
- Low Collector to Emitter Saturation Voltage
- High Speed Switching
- High Allowable Power Dissipation
- AEC-Q101 Qualified and PPAP Capable
- Pb-Free, Halogen Free and RoHS Compliant
- Ultra Small Package Facilitates Miniaturization in End Products

Typical Applications

- High Side Switch
- Lighting, Infotainment

ABSOLUTE MAXIMUM RATINGS at T_A = 25°C

Symbol	Value	Unit
V_{CBO}	-180	V
V _{CEO}	-160	V
V _{EBO}	-6	V
I _C	-1	Α
I _{CP}	-2	Α
P _C	0.42	W
Tj	150	°C
Tstg	-55 to +150	°C
	V _{CBO} V _{CEO} V _{EBO} I _C I _{CP} P _C Tj	V _{CBO} -180 V _{CEO} -160 V _{EBO} -6 I _C -1 I _{CP} -2 P _C 0.42 Tj 150

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on ceramic substrate. (250 mm² x 0.8 mm)

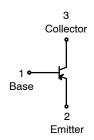


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ELECTRICAL CONNECTION



MARKING DIAGRAM



CMM = Specific Device Code M = Single Digit Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

				Value		
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = -120 V, I _E = 0 A			-0.1	μΑ
Emitter Cutoff Current	I _{EBO}	$V_{EB} = -4 \text{ V, } I_C = 0 \text{ A}$			-0.1	μΑ
DC Current Gain	h _{FE1}	$V_{CE} = -5 \text{ V},$ $I_{C} = -100 \text{ mA}$	100		400	
	h _{FE2}	$V_{CE} = -5 \text{ V},$ $I_{C} = -10 \text{ mA}$	90			
Gain-Bandwidth Product	f _T	V _{CE} = -10 V, I _C = -50 mA		120		MHz
Output Capacitance	Cob	V _{CB} = -10 V, f = 1 MHz		11		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)1	I _C = -250 mA, I _B = -25 mA		-0.1	-0.5	V
	V _{CE} (sat)2	I _C = -250 mA, I _B = -50 mA		-0.08	-0.13	V
Base to Emitter Saturation Voltage	V _{BE} (sat)	I _C = -250 mA, I _B = -25 mA		-0.8	-1.2	V
Collector to Base Breakdown Voltage	V _{(BR)CBO}	$I_C = -10 \mu A, I_E = 0 A$	-180			V
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = -1$ mA, $R_{BE} = \infty$	-160			V
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	$I_E = -10 \mu A,$ $I_C = 0 A$	-6			V
Turn-On Time	t _{on}	See Figure 1		90		ns
Storage Time	t _{stg}			1000		ns
Fall Time	t _f			70		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

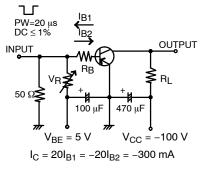


Figure 1. Switching Time Test Circuit

TYPICAL CHARACTERISTICS

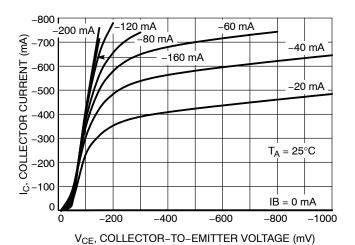
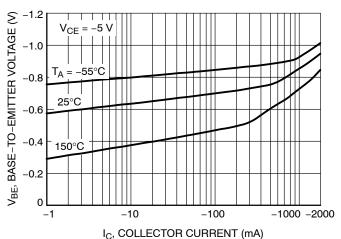


Figure 2. I_C vs. V_{CE}



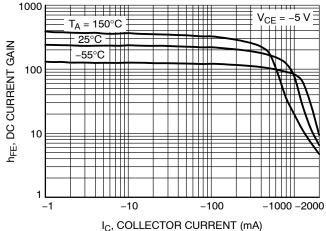


Figure 3. V_{BE} vs. I_{C}

Figure 4. h_{FE} vs. I_C

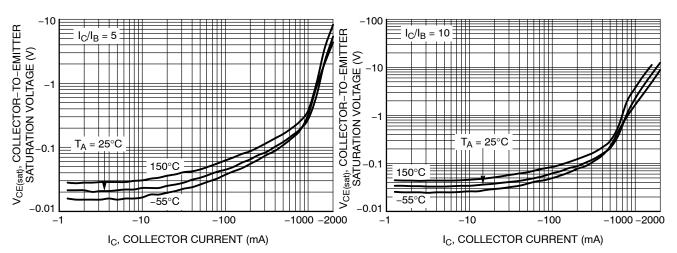


Figure 5. V_{CE(sat)} vs. I_C

Figure 6. V_{CE(sat)} vs. I_C

TYPICAL CHARACTERISTICS

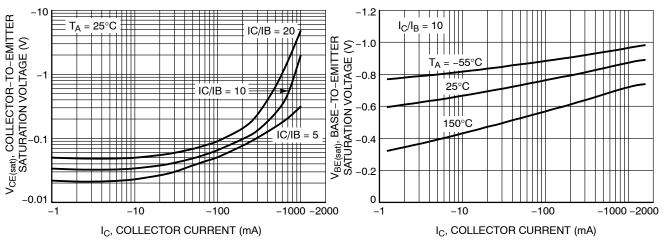


Figure 7. V_{CE(sat)} vs. I_C

Figure 8. V_{BE(sat)} vs. I_C

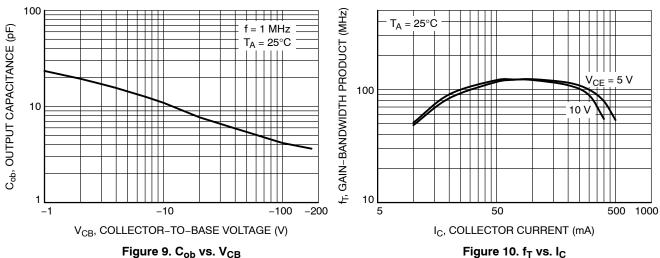


Figure 9. Cob vs. VCB

0.5

0.4

0.3

0.2

0

Mounted on ceramic

board 250 mm² x 0.8 mm

50

P_D, POWER DERATING (W)

IC, COLLECTOR CURRENT (A) 1 ms 0.1 10 ms T_A = 25°C 100 ms 0.01 Single Pulse Mounted on ceramic $DC \pm$ board 250 mm² x 0.8 mm 0.001 0.01 0.1 10 1000 V_{CE}, COLLECTOR-TO-EMITTER VOLTAGE (V)

T_A, AMBIENT TEMPERATURE (°C) Figure 11. Power Derating

100

Figure 12. Safe Operating Area

150

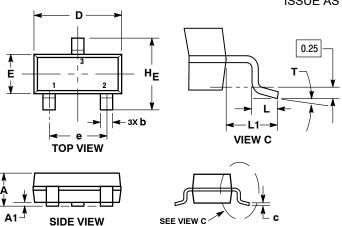
ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing) †
NSVT1418LT1G	СММ	SOT-23 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUF AS



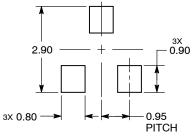
END VIEW

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M. 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

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